IN THE CLAIMS:

1. (currently amended) A crystalline material characterized in that it does not contain fluorides, with a composition in a roasted state corresponding to that of the material called ITQ-17 and in that it has a composition on an anhydrous base and in terms of moles of oxides upon being synthesized, unroasted, represented by: xX_2O_3: $(1-z)YO_2$: $zGeO_2$: r/n R_nO wherein:

X is at least one trivalent element,

Y is one or more tetravalent elements other than germanium,

R is an organic structure directing compound,

x varies between 0 and 0.02, ~~preferably between 0 and 0.01,~~

z is comprised between 0.02 and 0.67, ~~preferably between 0.04 and 0.5,~~

r varies between 0.01 and 0.5, ~~preferably between 0.01 and 0.25,~~ and

n is 1 or 2,

and whose most representative values of the X-ray diffraction angle are the following:

2θ +/- 0.5 (degrees)	Intensity (I/Io)
6.89	w, m
9.57	vs
19.35	m
21.37	m
21.90	vs

vs: very strong, m: medium, w: weak.

2. (currently amended) A crystalline material according to claim 1, whose composition on an anhydrous base and in terms of moles of oxide upon being synthesized, unroasted, may be represented by:

xX_2O_3: tTO_2 : $(1-z-t)SiO_2$: $zGeO_2$: r/n R_nO

wherein:

T is one or more tetravalent elements other than Ge or Si,

t varies between 0 and 0.15, ~~preferably between 0 and 0.10,~~ and

z is comprised between 0.02 and 0.67~~, preferably between 0.04 and 0.5, and "x", "X", "R", "r" and "n" have the meaning given in claim 1~~.

3. (previously presented) A crystalline material according to claim 1 or 2, wherein R is the cation 1-methyl-4-aza, 1-azoniumbicyclo [2.2.2] octane ($DABMe^+$).

4. (previously presented) A crystalline material according to claim 1 or 2, wherein R is the cation 1,4-bis[N-(4-aza, 1-azoniumbicyclo [2,2,2] octane) methyl]benzene $(d\text{-}DABBz)^{2+}$.

5. (currently amended) A crystalline material according to claim 1 wherein Y is one or more tetravalent elements selected ~~among~~ from the group consisting of Si, Sn, Ti ~~and~~ V and mixtures thereof.

6. (previously presented) A crystalline material according to claim 1 wherein Y is Si.

7. (currently amended) A crystalline material according to claim 1 or 2, wherein X is one or more trivalent ~~elements~~ element selected from the group consisting of B, Al, In, Ga, Fe and Cr.

8. (currently amended) A crystalline material according to claim 2, wherein T is one or more tetravalent elements selected ~~between~~ from the group consisting of V, Sn, ~~and~~ Ti and mixtures thereof .

9. (currently amended) A crystalline material according to claim 2, whose composition expressed in molar ratios is the following:

$ROH/(SiO_2+GeO_2+TO_2)$ is between 0.5 and 0.01, ~~preferably between 0.25 and 0.01~~

$GeO_2/(SiO_2+GeO_2+TO_2)$ is between 0.67 and 0.02, ~~preferably between 0.5 and 0.04~~

$(SiO_2+GeO_2+TO_2)/X_2O_3$ is between ∞ and 50, ~~preferably between .infin. and 100~~ and

$TO_2/(SiO_2+GeO_2+TO_2)$ is between 0.15 and 0~~, preferably between 0.1 and 0~~.

10. (currently amended) A crystalline material according to claim 2, whose composition expressed in molar ratios is the following:

$R(OH)_2/(SiO_2+GeO_2+TO_2)$: between 0.25 and 0.005, ~~preferably between 0.125 and 0.005~~

GeO2/$(SiO_2+GeO_2+TO_2)$: between 0.67 and 0.02, ~~preferably between 0.5 and 0.04~~

$(SiO_2+GeO_2+TO_2)/X_2O_3$: between ∞ and 50, ~~preferably between ∞ and 100~~

$TO_2/(SiO_2+GeO_2+TO_2)$: between 0.15 and 0~~, preferably between 0.1 and 0~~.

11. (currently amended) A process for synthesizing a crystalline material that does not contain fluorides, with a composition in a roasted state corresponding to that of the material called ITQ-17 and in that it has a composition on an anhydrous base and in terms of moles of oxides upon being synthesized, unroasted, represented by:

xX_2O_3: $(1-z)YO_2$: $zGeO_2$: r/n R_nO

wherein:

X is at least one trivalent element,

Y is one or more tetravalent elements other than germanium,

R is an organic structure directing compound,

x varies between 0 and 0.02, ~~preferably between 0 and 0.01,~~

z is comprised between 0.02 and 0.67, ~~preferably between 0.04 and 0.5,~~

r varies between 0.01 and 0.5, ~~preferably between 0.01 and 0.25,~~ and

n is 1 or 2,

and whose most representative values of the X-ray diffraction angle are the following:

2θ +/- 0.5 (degrees)	Intensity (I/Io)
6.89	w, m
9.57	vs
19.35	m
21.37	m
21.90	vs

vs: very strong, m: medium, w: weak,

and whose process comprises:

a) preparing a synthesis mixture that comprises at least:

a source of one or several tetravalent elements included under the name Y,

a source of Ge,

a source of at least one structure directing agent, and water;

b) keeping the synthesis mixture at temperatures between 100 and 200° C, until the crystalline material is formed, and

c) recovering the crystalline material.

12. (previously presented) A process according to claim 11, wherein the source of germanium and of the rest of the tetravalent elements is an oxide.

13. (currently amended) A process according to claim 11, wherein the synthesis mixture also comprises a source selected ~~among~~ from the group consisting of :

a source of one or more trivalent elements, X,

a source of one or more tetravalent elements other than Si and Ge, and

~~a mixture of both~~ mixtures thereof.

14. (currently amended) A process according to claim 11, wherein the source of the structure directing agent, R, is 1-methyl-4-aza, 1-azoniumbicyclo [2,2,2] octane hydroxide (DABMeOH), and wherein the synthesis mixture has a composition expressed in terms of molar ratios in the following intervals:

$H_2O/(YO_2+GeO_2)$: between 100 and 0.01, ~~preferably between 50 and 0.1,~~

$OH^-/(YO_2+GeO_2)$: between 3 and 0.01, ~~preferably between 1 and 0.03,~~

$R/(YO_2+GeO_2)$: between 3 and 0.01, ~~preferably between 1 and 0.03,~~

$GeO_2/(YO_2+GeO_2)$: between 0.67 and 0.02, ~~preferably between 0.5 and 0.04,~~ and

$(YO_2+GeO_2)/X_2O_3$: between ∞ and 50~~, preferably between ∞ and 100~~.

15. (currently amended) A process according to claim 11, wherein the source of the structure directing agent, R, is 1,4-bis[N-(4-aza, 1-azoniumbicyclo [2,2,2] octane) methyl]benzene hydroxide (d-DABBz(OH) 2), and wherein the synthesis mixture has a composition expressed in terms of molar ratios in the following intervals:

$H_2O/(YO_2+GeO_2)$: between 100 and 0.01, ~~preferably between 50 and 0.1,~~ OH.sup.- YO_2+GeO_2): between 3 and 0.01, ~~preferably between 1 and 0.03,~~ $R/(YO_2+GeO_2)$: between 1.5 and 0.005, ~~preferably between 0.5 and 0.015,~~ GeO_2/YO_2+GeO_2-): between 0.657 and 0.02, ~~preferably between 0.5 and 0.04,~~ $(YO_2+GeO_2)/X_2O_3$: between ∞ and 50~~, preferably between ∞ and 100~~.

16. (currently amended) A process according to claim 11, for preparing a material whose composition may be represented by the formula:

xX_2O_3: tTO_2: $(1-z-t)SiO_2$: $zGeO_2$: r/n R_nO

wherein:

T is one or more tetravalent elements other than Ge or Si,

t varies between 0 and 0.15, preferably between 0 and 0.10,

z is comprised between 0.02 and 0.67, ~~preferably between 0.04 and 0.5, and "x", "X", "R", "r" and "n" have the meaning given in claim 1,~~ that comprises:

a) preparing a synthesis mixture that comprises at least: a source of silicon, a source of Ge, and a source of at least one structure directing agent (R) and water

b) keeping the synthesis mixture at temperatures between 100 and 200° C, until the crystalline material is formed, and

c) recovering the crystalline material.

17. (currently amended) A process according to claim 16, wherein the source of the structure directing agent (R) is 1-methyl-4-aza, 1-azoniumbicyclo [2,2,2] octane hydroxide (DABMeOH), and wherein the synthesis mixture has a composition expressed in terms of molar ratios in the following intervals:

$H_2O/(SiO_2+GeO_2+TO_2)$: between 100 and 0.01, ~~preferably between 50 and 0.1,~~ $OH^-/(SiO_2+GeO_2+TO_2)$: between 3 and 0.01, ~~preferably between 1 and 0.03,~~

$R/(SiO_2+GeO_2+TO_2)$- : between 3 and 0.01, ~~preferably between 1 and 0.03,~~

$GeO_2/(SiO_2+GeO_2+TO_2)$: between 0.67 and 0.02, ~~preferably between 0.5 and 0.04,~~

$(SiO_2+GeO_2+TO_2)/X_2O_3$: between ∞ and 50, preferably ~~between ∞ and 100,~~ and

$TO_2/(SiO_2+GeO_2+TO_2)$: between 0.15 and 0~~, preferably between 0.1 and 0~~.

18. (currently amended) A process according to claim 16, wherein the structure directing agent, R, is 1,4-bis[N-(4-aza, 1-azoniumbicyclo [2,2,2] octane) methyl]benzene hydroxide (d-DABBz$(OH)_2$), and wherein the synthesis mixture has a composition expressed in terms of molar ratios in the following intervals:

$H_2O/(SiO_2+GeO_2+TO_2)$: between 100 and 0.01, ~~preferably between 50 and 0.1~~ $OH^-/(SiO_2+GeO_2+TO_2)$: between 3 and 0.01, ~~preferably between 1 and 0.03~~

$R/(SiO_2+GeO_2+TO_2)$: between 1.5 and 0.005, ~~preferably between 0.5 and 0.015~~

$GeO_2/(SiO_2+GeO_2+TO_2)$: between 0.67 and 0.02, ~~preferably between 0.5 and 0.04~~

$(SiO_2+GeO_2+TO_2)/X_2O_3$: between ∞ and 50, ~~preferably between ∞ and 100,~~

$TO_2/(SiO_2+GeO_2+TO_2)$: between 0.15 and 0~~, preferably between 0.1 and 0~~.

19. (currently amended) A process according to claim 16, wherein the synthesis mixture comprises one or more tetravalent elements, T, selected ~~among~~ from the group consisting of V, Sn, ~~and~~ Ti, and mixtures thereof.

20. (previously presented)A process according to claim 16, wherein the source of germanium, silicon and the rest of the tetravalent elements is an oxide.

21. (previously presented) A process according to claim 16, wherein the synthesis mixture also comprises a source of one or more trivalent elements, X.

22. (currently amended) A process according to claim 11 or 16 that also comprises a step of post-synthesis treatment of the material, whereby the organic component is removed from the structure by means of a technique selected ~~among~~ from the group consisting of extraction, roasting and both.

23. (currently amended) A material obtained according to the process of claim 22, characterized in that its diffraction diagram has the following as the most important lines:

2θ +/- 0.5 (degrees)	Intensity (I/Io)
6.89	w, m
9.59	vs
21.27	m
21.87	m
27.87	vs.

24. (new) A crystalline material according to claim 1 wherein x varies between 0 and 0.01.

25. (new) A crystalline material according to claim 1 wherein z is comprised between 0.04 and 0.5.

26. (new) A crystalline material according to claim 1 wherein r varies between 0.01 and 0.25.

27. (new) A crystalline material according to claim 1 wherein x varies between 0 and 0.01, z is comprised between 0.04 and 0.5, and r varies between 0.01 and 0.25.

28. (new) A crystalline material according to claim 2 wherein t varies between 0 and 0.10.

29. (new) A crystalline material according to claim 2 wherein z is comprised between 0.04 and 0.5.

30. (new) A crystalline material according to claim 2 wherein t varies between 0 and 0.10, and z is comprised between 0.04 and 0.5.

31. (new) A process for synthesizing a crystalline material that does not contain fluorides according to claim 11 wherein x varies between 0 and 0.01.

32. (new) A process for synthesizing a crystalline material that does not contain fluorides according to claim 11 wherein z is comprised between 0.04 and 0.5.

33. (new) A process for synthesizing a crystalline material that does not contain fluorides according to claim 11 r varies between 0.01 and 0.25.

34. (new) A process for synthesizing a crystalline material that does not contain fluorides according to claim 11 wherein x varies between 0 and 0.01, z is comprised between 0.04 and 0.5, and r varies between 0.01 and 0.25.